

64 Megabit 3.3 Volt CMOS FLASH EEPROM

DP3Z4MX16PMTY5 / DP3Z4MX16PMBY5

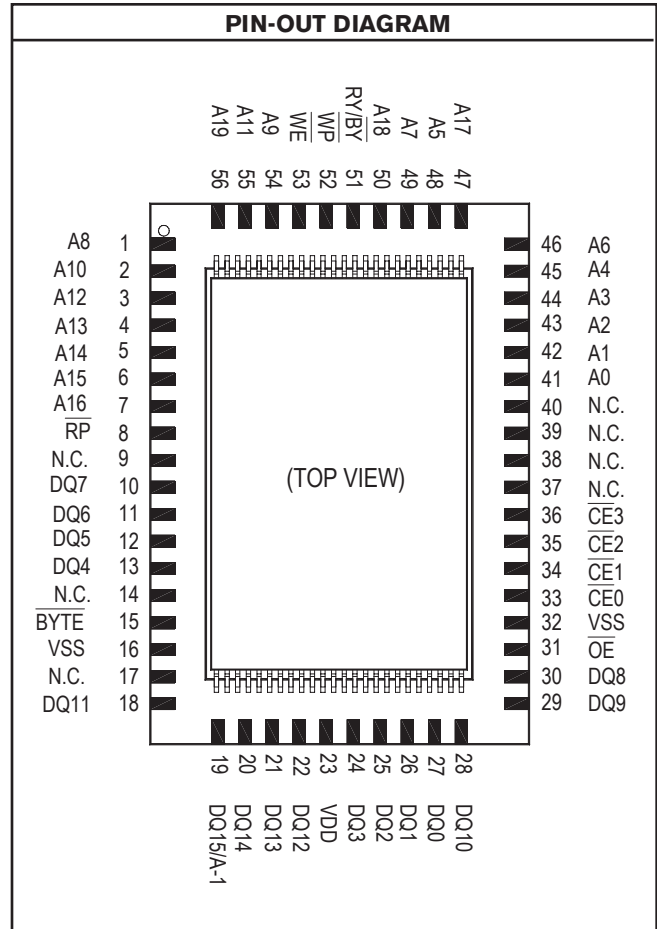
DESCRIPTION:

The DP3Z4MX16PMTY5 / DP3Z4MX16PMBY5 is a 64 megabit 3.3 volt only CMOS Flash EEPROM (Electrically In-System Programmable and Erasable ROM Memory) stack. These stacks are constructed of four 1M x 16 FLASH EEPROM's that are configured as a 4M x 16.

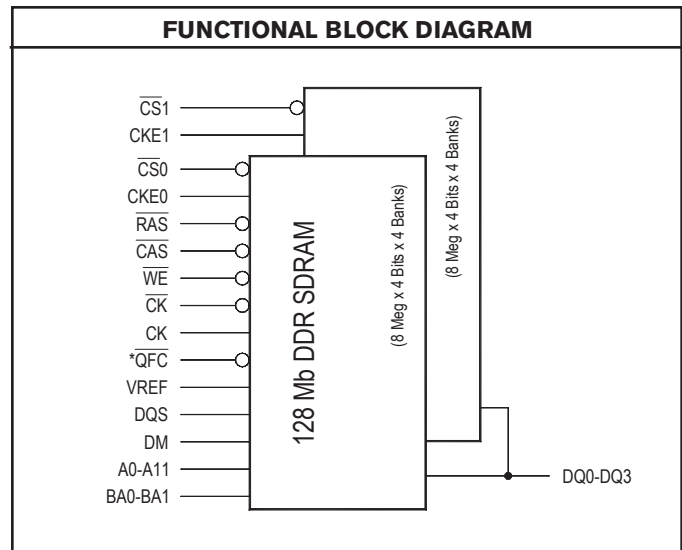
The module features high speed access times with common data inputs and outputs. The flash devices used in this module also features BGO (Blank Ground Operations). This feature allows Program or Erase operations to be performed on one bank of the device while a read operation is performed on the other bank.

FEATURES:

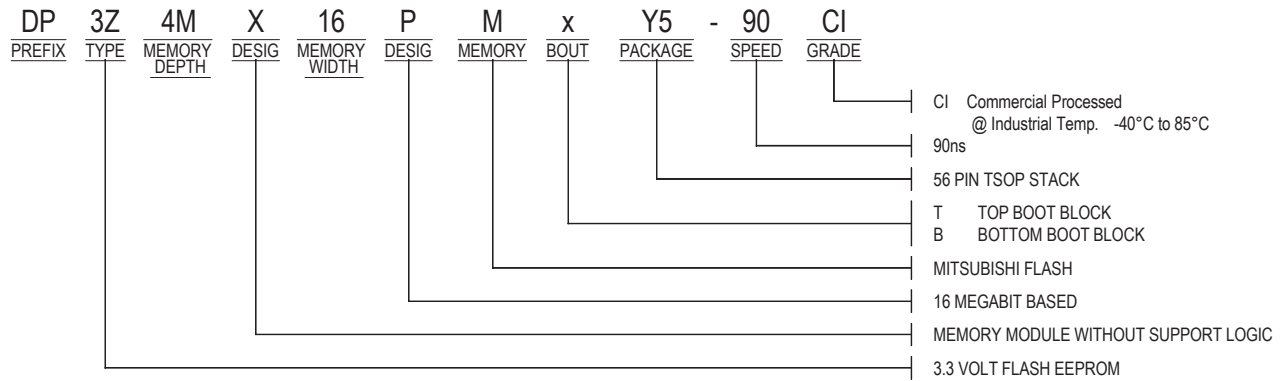
- Organizations Available: 4M x 16
- Fast Read Access Times: 80ns ($V_{DD}=3.3 \pm 0.3V$)
90ns ($V_{DD} 2.7\sim 3.6V$)
- Industrial Temperature: $-40^{\circ}C$ to $+85^{\circ}C$
- Low Power:
 - 70 mA Maximum active (16 bit Mode)
 - 20 μA Maximum Standby (CMOS)
- 100K Program / Erase Sysles
- 3.3 Volt Only In-System Programming
- Package: 56-Pin TSOP Stack



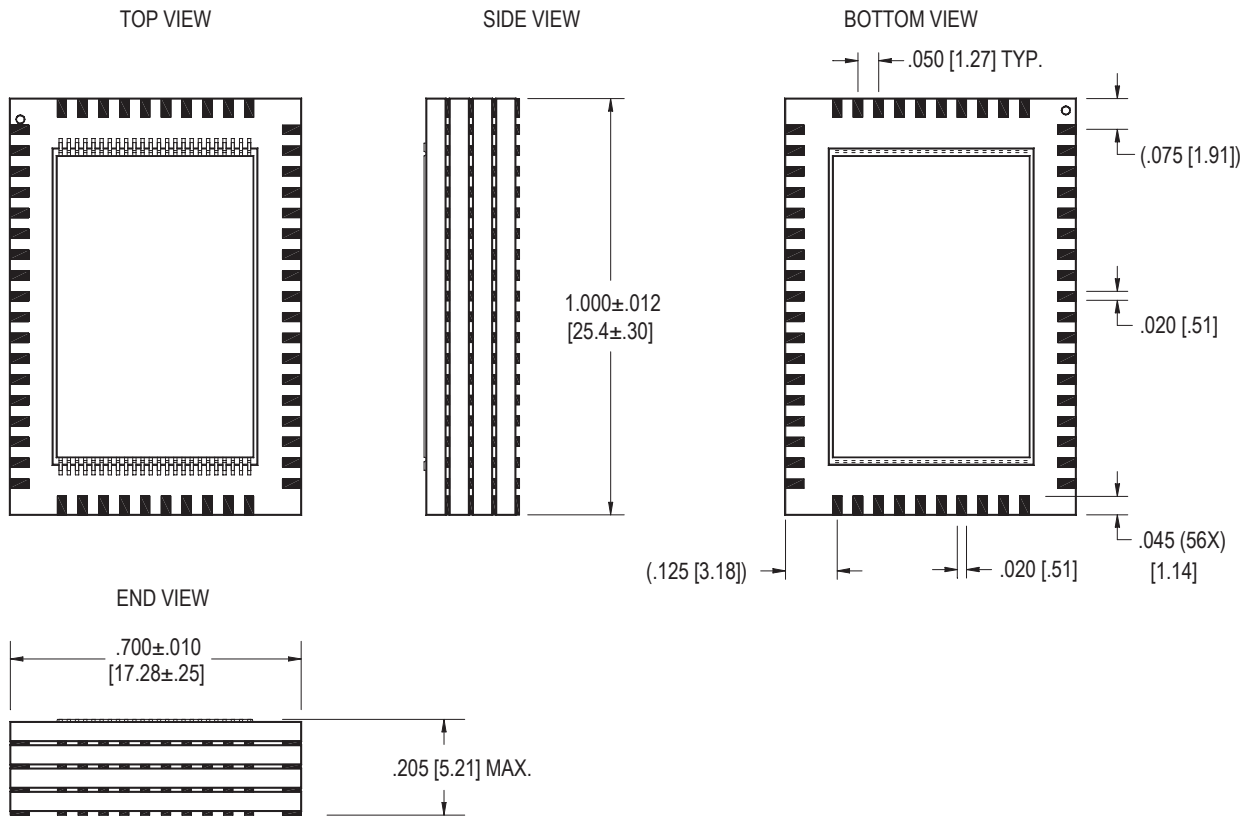
PIN NAMES	
A0 - A19	Address
DQ0 - DQ15	Data In/Data Out
$\overline{CE}0, \overline{CE}1$	Low Chip Enables
\overline{WE}	Write Enable
\overline{OE}	Output Enable
\overline{WP}	Write Protect
\overline{RP}	Reset/Power Down
BYTE	Byte Enable
RY/ \overline{BY}	Ready/Busy
VDD	Power Supply (+3.3V)
Vss	Ground
N.C.	No Connect



ORDERING INFORMATION



MECHANICAL DRAWING



P R E L I M I N A R Y